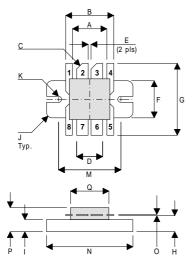
## **TetraFET**

# D1018UK



## **ROHS COMPLIANT METAL GATE RF SILICON FET**

### **MECHANICAL DATA**



#### DD

- SOURCE (COMMON) PIN 2 PIN 1 DRAIN 1 SOURCE (COMMON) PIN 3 DRAIN 2 PIN 4 PIN 5 SOURCE (COMMON) PIN 6 GATE 2 GATE 1
- PIN 7

PIN 8 SOURCE (COMMON)

				(-
DIM	mm	Tol.	Inches	Tol.
А	9.14	0.13	0.360	0.005
В	12.70	0.13	0.500	0.005
С	45°	5°	45°	5°
D	6.86	0.13	0.270	0.005
Е	0.76	0.13	0.030	0.005
F	9.78	0.13	0.385	0.005
ŋ	19.05	0.25	0.750	0.010
Н	4.19	0.13	0.165	0.005
Ι	3.17	0.13	0.125	0.005
L	1.52R	0.13	0.060R	0.005
Κ	1.65R	0.13	0.065R	0.005
М	16.51	0.13	0.650	0.005
Ν	22.86	0.13	0.900	0.005
0	0.13	0.02	0.005	0.001
Ρ	6.35	0.64	0.250	0.025
Q	10.77	0.13	0.424	0.005

## GOLD METALLISED **MULTI-PURPOSE SILICON DMOS RF FET** 100W - 28V - 500MHz **PUSH-PULL**

## FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C<sub>rss</sub>
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN 10 dB MINIMUM

### APPLICATIONS

 HF/VHF/UHF COMMUNICATIONS from 1 MHz to 500 MHz

## ABSOLUTE MAXIMUM RATINGS (T<sub>case</sub> = 25°C unless otherwise stated)

P <sub>D</sub>	Power Dissipation	250W
BV <sub>DSS</sub>	Drain – Source Breakdown Voltage *	70V
BV <sub>GSS</sub>	Gate – Source Breakdown Voltage *	±20V
I <sub>D(sat)</sub>	Drain Current *	15A
T <sub>stg</sub>	Storage Temperature	–65 to 150°C
Tj	Maximum Operating Junction Temperature	200°C

\* Per Side



### ELECTRICAL CHARACTERISTICS (T<sub>case</sub> = 25°C unless otherwise stated)

Parameter		Test	Min.	Тур.	Max.	Unit	
PER SIDE							
BVaca	Drain–Source	$V_{GS} = 0$	I <sub>D</sub> = 100mA	70			V
BV <sub>DSS</sub>	Breakdown Voltage	VGS – 0	D = 100 MA	10			v
I <sub>DSS</sub>	Zero Gate Voltage	1/2 = -281/2				3	mA
	Drain Current	$V_{DS} = 28V$	V <sub>GS</sub> = 0			3	ma
I <sub>GSS</sub>	Gate Leakage Current	$V_{GS} = 20V$	$V_{DS} = 0$			1	μA
V <sub>GS(th)</sub>	Gate Threshold Voltage *	I <sub>D</sub> = 10mA	$V_{DS} = V_{GS}$	1		7	V
9 <sub>fs</sub>	Forward Transconductance *	V <sub>DS</sub> = 10V	I <sub>D</sub> = 3A	2.4			S
TOTAL DEVICE							
G <sub>PS</sub>	Common Source Power Gain	P <sub>O</sub> = 100W		10			dB
η	Drain Efficiency	V <sub>DS</sub> = 28V	I <sub>DQ</sub> = 1.2A	50			%
VSWR	Load Mismatch Tolerance	f = 500MHz		20:1			_
PER SIDE							
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 28V	$V_{GS} = -5V f = 1MHz$			180	pF
C <sub>oss</sub>	Output Capacitance	V <sub>DS</sub> = 28V	$V_{GS} = 0$ f = 1MHz			90	pF
C <sub>rss</sub>	Reverse Transfer Capacitance	V <sub>DS</sub> = 28V	$V_{GS} = 0$ f = 1MHz			7.5	pF

\* Pulse Test: Pulse Duration = 300  $\mu s$  , Duty Cycle  $\leq 2\%$ 

### HAZARDOUS MATERIAL WARNING

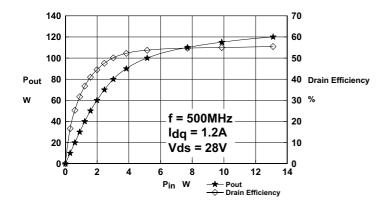
The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

#### THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

#### THERMAL DATA

R <sub>THj-case</sub>	Thermal Resistance Junction – Case	Max. 0.7°C / W
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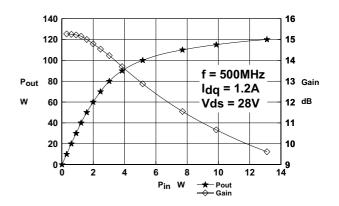
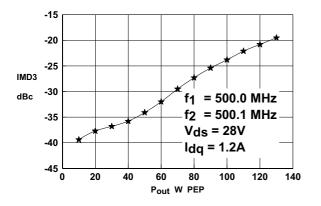


Figure 1 Power Output and Efficiency vs Input Power

Figure 2 Power Output and Gain vs Input Power



Frequency Z<sub>S</sub> Z<sub>L</sub>

**OPTIMUM SOURCE AND LOAD IMPEDANCE** 

MHz	Ζ <sub>S</sub> Ω	ΖL Ω	
500	2.0 - j2.2	2.6 - j0.6	

N.B. Impedances measured terminal to terminal

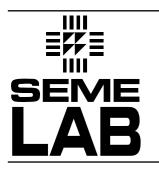
Figure 3 IMD vs. Output Power



## **Typical S Parameters**

! Vds=28V, Idq=0.3A # MHZ S MA R 50

!Freq	S11	S21		S12		S22
!MHz	mag ang	mag	ang	mag	ang	mag ang
100	0.86 -157.3	5.98	55.7	0.01	20.3	0.73 -139.7
150	0.9 -163.2	3.22	43.1	0.01	78	0.82 -149.7
200	0.93 -167.9	1.98	36.9	0.02	98.2	0.88 -156.3
250	0.95 -170.4	1.39	31	0.03	101	0.91 -160.2
300	0.95 -172.7	1.1	29.6	0.05	103.7	0.93 -163.6
350	0.96 -174.5	0.82	23.9	0.06	99.9	0.94 -166.1
400	0.96 -176.2	0.69	23.9	0.08	100.2	0.95 -168.1
450	0.97 -177.5	0.55	22.1	0.09	98.3	0.96 -170.1
500	0.97 -179.4	0.51	21	0.11	95.6	0.97 -171.6
550	0.97 179.8	0.43	19.1	0.13	90.8	0.97 -173.3
600	0.96 178.8	0.4	15.1	0.15	82	0.97 -174.5
650	0.98 177.5	0.35	15.8	0.17	83.5	0.98 -175.7
700	0.99 175.4	0.31	11	0.19	76.8	1 -178.4
750	0.99 173	0.27	14.2	0.21	75.1	1.01 178.8
800	1 170.5	0.24	16.6	0.22	71.5	1 176.1
850	0.99 168.1	0.24	22.7	0.25	72.6	0.99 173.3
900	1 166.1	0.24	23.7	0.3	68.8	0.99 170.6
950	1 163.9	0.25	23.2	0.34	62.7	0.97 167.7
1000	0.99 161.6	0.25	21.7	0.37	56.4	0.96 166.1



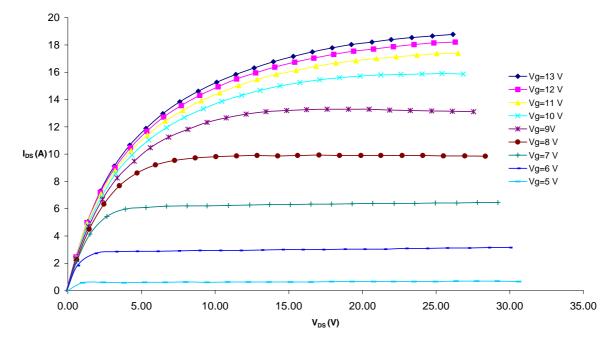
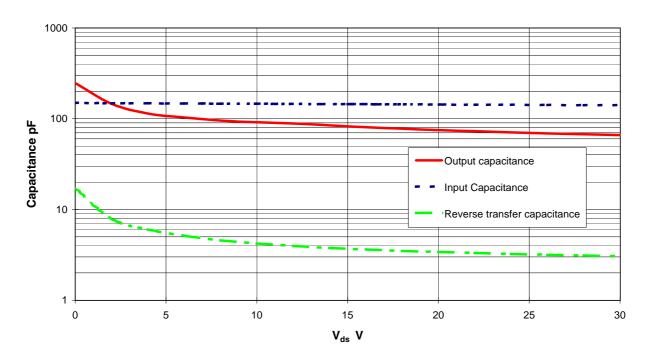
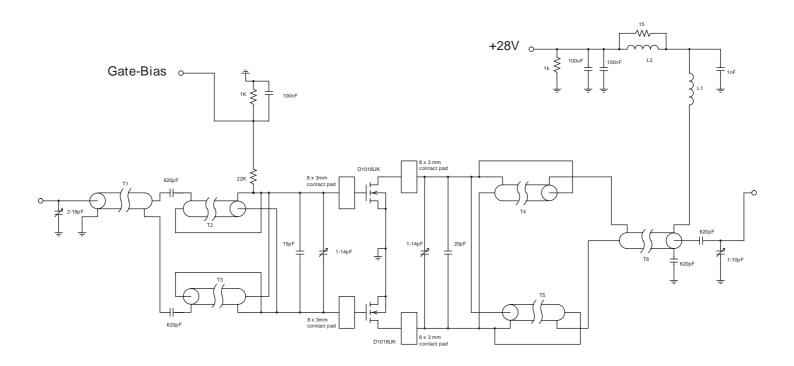


Figure 4 – Typical IV Characteristics.









## **500MHz TEST FIXTURE**

- T1,6 65mm 50ohm UT85 semi-rigid coax
- T2,3,4,5 75mm 15 ohm UT85-15 semi-rigid coax
- L1 6 turns 21 swg enamelled copper wire, 3mm id.
- L2 8.5 turns 19swg enamelled copper wire on Fair-Rite FT82-43 core
- T6 Placed through Ferronics 12-360-K ferrite bead